KSD80N06

60V N-Channel MOSFET

General Description

The KSD80N06 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate char ge for most of the synchronous buck converter applications

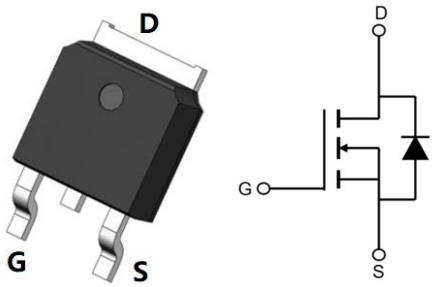
Product Summary

V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (A)
60	5.5 at V_{GS} = 10 V	80
	7.4 at V_{GS} = 4.5 V	60

Features

- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

TO-252 Pin Configuration



Applications

- Battery protection
- Load switch
- Uninterruptible power supply

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±25	V
I_D	Drain Current – Continuous (T_C=25℃)	80	A
	Drain Current – Continuous (T_C=100℃)	40	A
I_{DM}	Drain Current – Pulsed[1]	170	A
P_D	Power Dissipation (T_C=25℃)	55	W
	Power Dissipation (T_C=100℃)	1.0	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.84	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	5.5	7.1	mΩ
		V_{GS}=4.5V , I_D=10A	---	7.4	8.8	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
gfs	Forward Transconductance	V_{DS}=10V , I_S=15A	---	35	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=30V , V_{GS}=10V , I_D=10A	---	84	---	nC
Q_{gs}	Gate-Source Charge[2,3]		---	9.2	---	
Q_{gd}	Gate-Drain Charge[2,3]		---	17.5	---	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DS}=30V, I_D=10A V_{GS}=10V,R_G=3.3Ω	---	10.8	---	ns
T_r	Rise Time[2,3]		---	8.3	---	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	41	---	
T_f	Fall Time[2,3]		---	14	---	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , F=1MHz	---	3651	---	pF
C_{oss}	Output Capacitance		---	264	---	
C_{rss}	Reverse Transfer Capacitance		---	117	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	60	A
I_{SM}	Pulsed Source Current		---	---	150	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition：Tj=25℃, V_{DD}=15V,V_G=10V,L=0.5mH, Rg=25Ω

Typical Electrical and Thermal Characteristics (Curves)

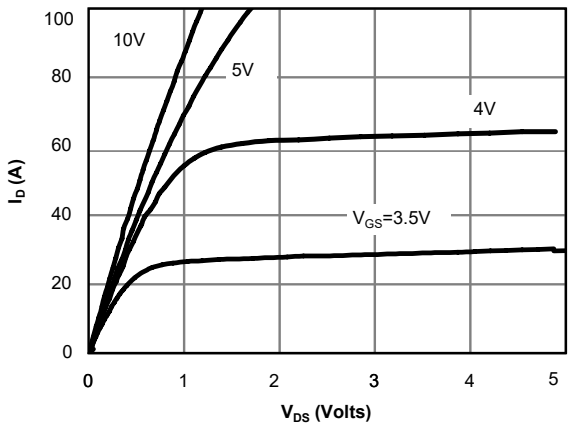


Fig 1: On-Region Characteristics

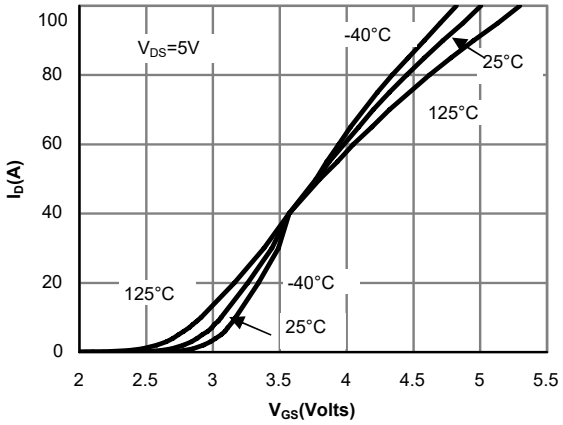


Figure 2: Transfer Characteristics

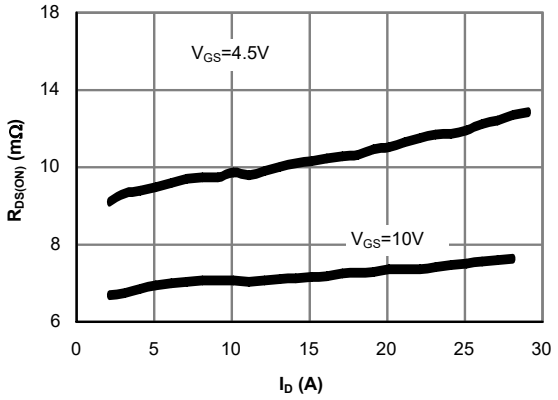


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

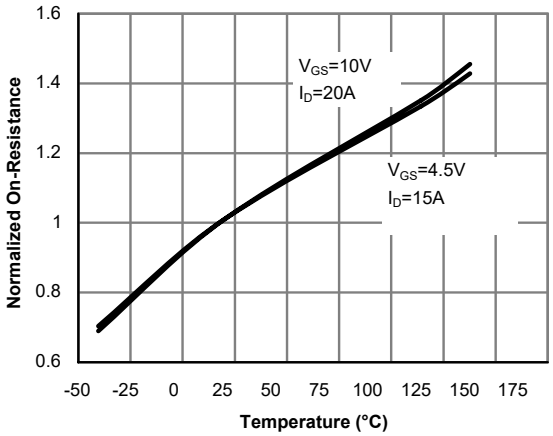


Figure 4: On-Resistance vs. Junction Temperature

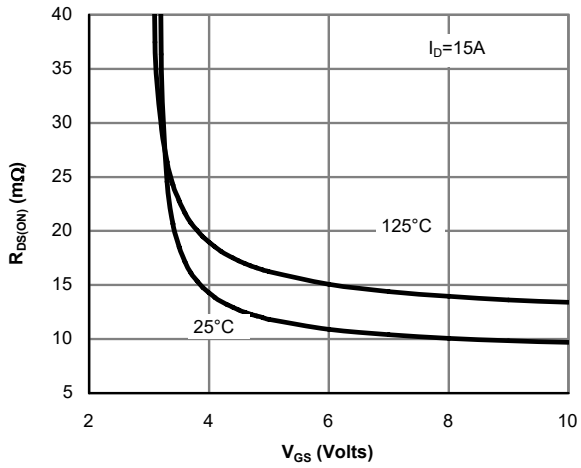


Figure 5: On-Resistance vs. Gate-Source Voltage

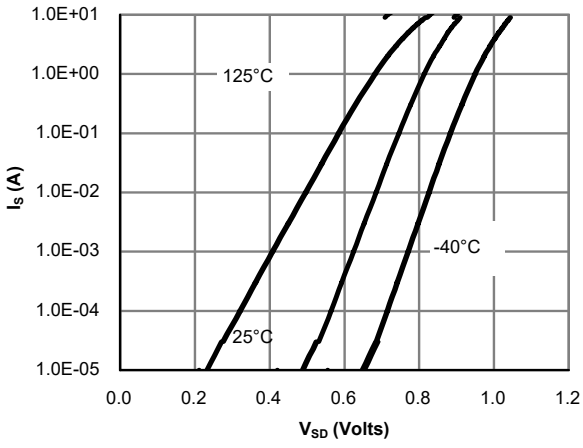


Figure 6: Body-Diode Characteristics

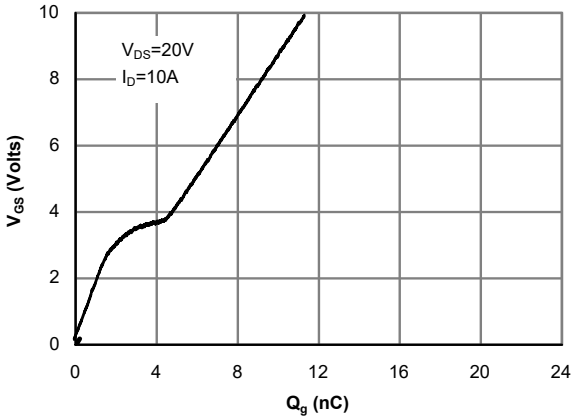


Figure 7: Gate-Charge Characteristics

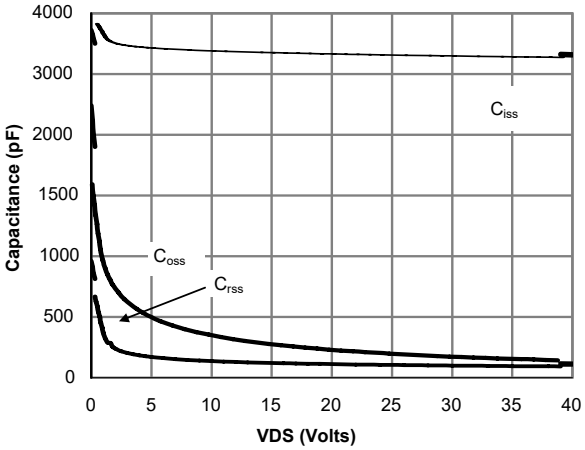


Figure 8: Capacitance Characte

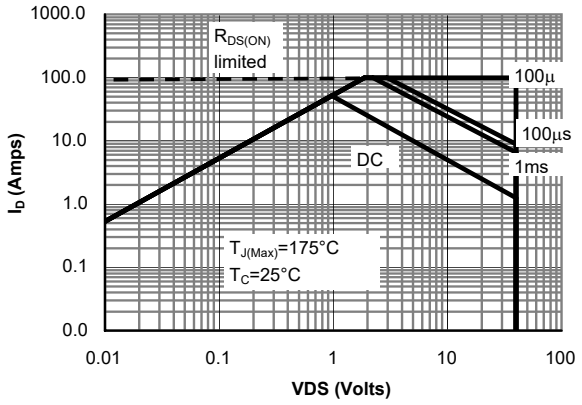


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

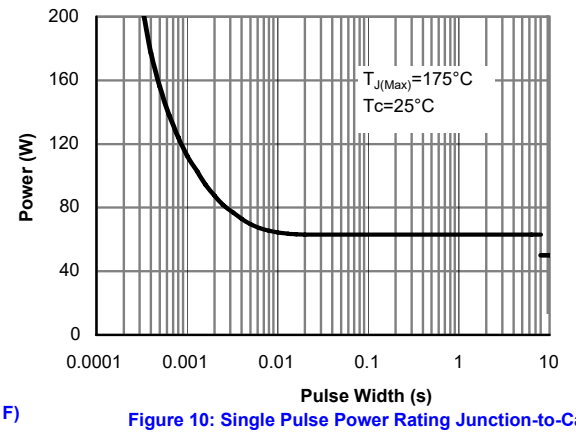


Figure 10: Single Pulse Power Rating Junction-to-Case

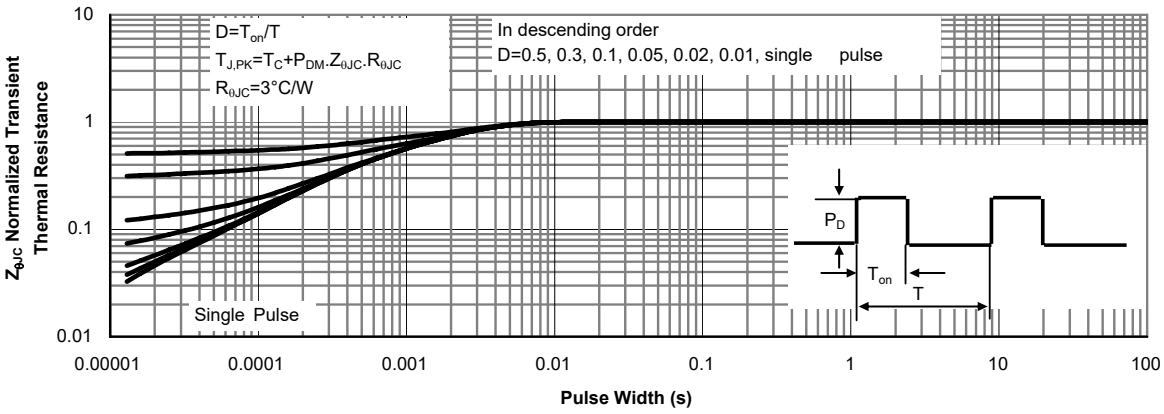


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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